# AN1V PB22

Current Sensor

Model Number:

AN1V 50 PB22

AN1V 100 PB22

AN1V 150 PB22

AN1V 200 PB22

AN1V 250 PB22
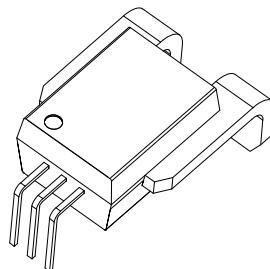
For the electronic measurement of current:DC,AC,pulsed...,with galvanic separation between the primary and the secondary circuit.

Features

- ✧ Open loop current sensor using the Hall effect
- ✧ ASIC Technology
- ✧ Maintain output proportional to changes in the power supply（include offset and sensitivity）
- ✧ Galvanic separation between primary and secondary
- ✧ Insulating plastic case recognized according to UL 94-V0
- ✧ No insertion losses
- ✧ Small size
- ✧ Standards:
  - ■ IEC 60664-1:2020
  - ■ IEC 61800-5-1:2022
  - ■ IEC 62109-1:2010

Applications

- ✧ AC variable speed
- ✧ Uninterruptible Power Supply (UPS)
- ✧ Static converters for DC motor drives
- ✧ Switch Mode Power Supplies (SMPS)
- ✧ Power supply for welding applications
- ✧ Battery Management
- ✧ Wind energy inverter

Safety

The sensor must be used according to IEC 61800-5-1.

The sensor must be used in electric/electronic equipment with respect to applicable standards and safety requirements in accordance with the following manufacture's operating instructions.

Caution,risk of electrical shock !

When operating the sensor, certain parts of the module can carry hazardous voltage (e.g., Primary busbar,power supply).

Ignore this warning can lead to injury and/or cause serious damage.

This sensor is a built-in device, whose conducting parts must be inaccessible after installation. A protective housing or additional shield could be used.

Main supply must be able to be disconnected.

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Absolute maximum ratings(not operating)

Parameter	Symbol	Unit	Value
Supply voltage	V_C	V	6.5
ESD rating, Human Body Model (HBM)	V_{ESD}	V	8000

※ Stresses above these ratings may cause permanent damage.

※ Exposure to absolute maximum ratings for extended periods may degrade reliability.

Environmental and mechanical characteristics

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Ambient operating temperature	T_A	℃	−40		150	AN1V 50 PB22
			−40		150	AN1V 100 PB22
			−40		125	AN1V 150 PB22
			−40		85	AN1V 200 PB22
			−40		85	AN1V 250 PB22
Ambient storge temperature	T_S	℃	−55		150	
Primary resistance value	R_P	μΩ		100		
Mass	m	g		5		

Insulation coordination

Parameter	Symbol	Unit	Value	Comment
Rms voltage for AC insulation test, @50Hz,1min	V_d	kV	4.8	According to IEC 60664-1
Plastic case	-	-	UL94-V0	
Comparative traking index	CTI	PLC	2	
Application example	-	-	475V_{RMS}	Reinforced insulation,according to IEC 61800-5-1, IEC 62109-1CATⅢ， PD2
Application example	-	-	960V_{RMS}	Basic insulation,according to IEC 61800-5-1, IEC 62109-1CATⅢ， PD2

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※ With T_A = 25℃, V_C = 5V, R_L = 10kΩ,unless otherwise noted.

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Electrical data						
Primary nominal rms current	I_{PN}	A	0		50	
Primary current measuring range	I_{PM}	A	0		50	
Supply voltage	V_C	V	4.5	5.0	5.5	
Output voltage	V_{OUT}	V	$V_{OUT} = V_{QOV} + G_{th} \times I_P \times (V_C/5)$			
Electrical offset voltage	V_{QOV}	V		$0.1 V_{CC}$		
Theoretical sensitivity	G_{th}	mV/A		80		
Current consumption	I_C	mA		8	11	
Load resistance	R_L	kΩ	5.1			
Load capacitor	C_2	nF		1	10	
Power filter capacitor	C_1	nF		100		
Performance data						
Sensitivity error	ε_G	%	–1		1	
Temperature of G	TCG	%	–1.5		1.5	@T_A=-40℃~150℃
Electrical offset current	V_{0E}	mV	–10	±5	10	@V_C=5V also I_P=0A
Electrical offset error of temperature drift	TCV_{0E}	mV	–10		10	@T_A=-40℃~150℃
Hysteresis offset voltage	V_{0M}	mV		4		@ V_C=5V, after ±I_{PN}
Linearity error	ε_L	% of I_{PN}	–1		1	Exclusive of V_{0E}
Accuracy@ I_{PN}	X	% of I_{PN}	–2		2	@T_A=-40℃~150℃
Response time @ 90% of I_{PN}	t_r	μs		2.5	5	@C_2=1nF
Frequency bandwidth(-3dB)	BW	kHz		250		@C_2=1nF
Output noise	Vno	mV		5		@C_2=1nF

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※ With T_A = 25℃, V_C = 5V, R_L = 10kΩ, unless otherwise noted.

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Electrical data						
Primary nominal rms current	I_{PN}	A	0		100	
Primary current measuring range	I_{PM}	A	0		100	
Supply voltage	V_C	V	4.5	5.0	5.5	
Output voltage	V_{OUT}	V	$V_{OUT}= V_{QOV} + G_{th} \times I_P \times (V_C/5)$			
Electrical offset voltage	V_{QOV}	V		$0.1 V_{CC}$		
Theoretical sensitivity	G_{th}	mV/A		40		
Current consumption	I_C	mA		8	11	
Load resistance	R_L	kΩ	5.1			
Load capacitor	C_2	nF		1	10	
Power filter capacitor	C_1	nF		100		
Performance data						
Sensitivity error	ε_G	%	–1		1	
Temperature of G	TCG	%	–1.5		1.5	@T_A=-40℃~150℃
Electrical offset current	V_{OE}	mV	–10	±5	10	@V_C=5V also I_P=0A
Electrical offset error of temperature drift	TCV_{OE}	mV	–10		10	@T_A=-40℃~150℃
Hysteresis offset voltage	V_{OM}	mV		4		@ V_C=5V, after ±I_{PN}
Linearity error	ε_L	% of I_{PN}	–1		1	Exclusive of V_{OE}
Accuracy@ I_{PN}	X	% of I_{PN}	–2		2	@T_A=-40℃~150℃
Response time @ 90% of I_{PN}	t_r	μs		2.5	5	@C_2=1nF
Frequency bandwidth(-3dB)	BW	kHz		250		@C_2=1nF
Output noise	Vno	mV		2.7		@C_2=1nF

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※ With T_A = 25℃, V_C = 5V, R_L = 10kΩ,unless otherwise noted.

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Electrical data						
Primary nominal rms current	I_{PN}	A	0		150	
Primary current measuring range	I_{PM}	A	0		150	
Supply voltage	V_C	V	4.5	5.0	5.5	
Output voltage	V_{OUT}	V	$V_{OUT}= V_{QOV} + G_{th} \times I_P \times (V_C/5)$			
Electrical offset voltage	V_{QOV}	V		$0.1 V_{CC}$		
Theoretical sensitivity	G_{th}	mV/A		26.66		
Current consumption	I_C	mA		8	11	
Load resistance	R_L	kΩ	5.1			
Load capacitor	C_2	nF		1	10	
Power filter capacitor	C_1	nF		100		
Performance data						
Sensitivity error	ε_G	%	–1		1	
Temperature of G	TCG	%	–1.5		1.5	@T_A=-40℃~125℃
Electrical offset current	V_{OE}	mV	–10	±5	10	@V_C=5V also I_P=0A
Electrical offset error of temperature drift	TCV_{OE}	mV	–10		10	@T_A=-40℃~125℃
Hysteresis offset voltage	V_{OM}	mV		4		@ V_C=5V, after ±I_{PN}
Linearity error	ε_L	% of I_{PN}	–1		1	Exclusive of V_{OE}
Accuracy@ I_{PN}	X	% of I_{PN}	–2		2	@T_A=-40℃~125℃
Response time @ 90% of I_{PN}	t_r	μs		2.5	5	@C_2=1nF
Frequency bandwidth(-3dB)	BW	kHz		250		@C_2=1nF
Output noise	Vno	mV		1.8		@C_2=1nF

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※ With T_A = 25℃, V_C = 5V, R_L = 10kΩ,unless otherwise noted.

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Electrical data						
Primary nominal rms current	I_{PN}	A	0		200	
Primary current measuring range	I_{PM}	A	0		200	
Supply voltage	V_C	V	4.5	5.0	5.5	
Output voltage	V_{OUT}	V	$V_{OUT}= V_{QOV} + G_{th} \times I_P \times (V_C/5)$	
Electrical offset voltage	V_{QOV}	V		$0.1V_{CC}$		
Theoretical sensitivity	G_{th}	mV/A		20		
Current consumption	I_C	mA		8	11	
Load resistance	R_L	kΩ	5.1			
Load capacitor	C_2	nF		1	10	
Power filter capacitor	C_1	nF		100		
Performance data						
Sensitivity error	ε_G	%	–1		1	
Temperature of G	TCG	%	–1.5		1.5	@T_A=–40℃~85℃
Electrical offset current	V_{0E}	mV	–10	±5	10	@V_C=5V also I_P=0A
Electrical offset error of temperature drift	TCV_{0E}	mV	–10		10	@T_A=–40℃~85℃
Hysteresis offset voltage	V_{0M}	mV		4		@ V_C=5V, after ±I_{PN}
Linearity error	ε_L	% of I_{PN}	–1		1	Exclusive of V_{0E}
Accuracy@ I_{PN}	X	% of I_{PN}	–2		2	@T_A=–40℃~85℃
Response time @ 90% of I_{PN}	t_r	μs		2.5	5	@C_2=1nF
Frequency bandwidth(-3dB)	BW	kHz		250		@C_2=1nF
Output noise	Vno	mV		1.4		@C_2=1nF

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※ With T_A = 25℃, V_C = 5V, R_L = 10kΩ,unless otherwise noted.

Parameter	Symbol	Unit	Min	Typ	Max	Comment
Electrical data						
Primary nominal rms current	I_{PN}	A	0		250	
Primary current measuring range	I_{PM}	A	0		250	
Supply voltage	V_C	V	4.5	5.0	5.5	
Output voltage	V_{OUT}	V	$V_{OUT}= V_{QOV} + G_{th} \times I_P \times (V_C/5)$			
Electrical offset voltage	V_{QOV}	V		$0.1 V_{CC}$		
Theoretical sensitivity	G_{th}	mV/A		16		
Current consumption	I_C	mA		8	11	
Load resistance	R_L	kΩ	5.1			
Load capacitor	C_2	nF		1	10	
Power filter capacitor	C_1	nF		100		
Performance data						
Sensitivity error	ε_G	%	–1		1	
Temperature of G	TCG	%	–1.5		1.5	@T_A=–40℃~85℃
Electrical offset current	V_{OE}	mV	–10	±5	10	@V_C=5V also I_P=0A
Electrical offset error of temperature drift	TCV_{OE}	mV	–10		10	@T_A=–40℃~85℃
Hysteresis offset voltage	V_{OM}	mV		4		@ V_C=5V, after ±I_{PN}
Linearity error	ε_L	% of I_{PN}	–1		1	Exclusive of V_{OE}
Accuracy@ I_{PN}	X	% of I_{PN}	–2		2	@T_A=–40℃~85℃
Response time @ 90% of I_{PN}	t_r	μs		2.5	5	@C_2=1nF
Frequency bandwidth(-3dB)	BW	kHz		250		@C_2=1nF
Output noise	Vno	mV		1.1		@C_2=1nF

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Dimensions(Unit mm)

Terminal definition：
1 VCC
2 GND
3 VOUT
4 IP+
5 IP−

Laser mark area
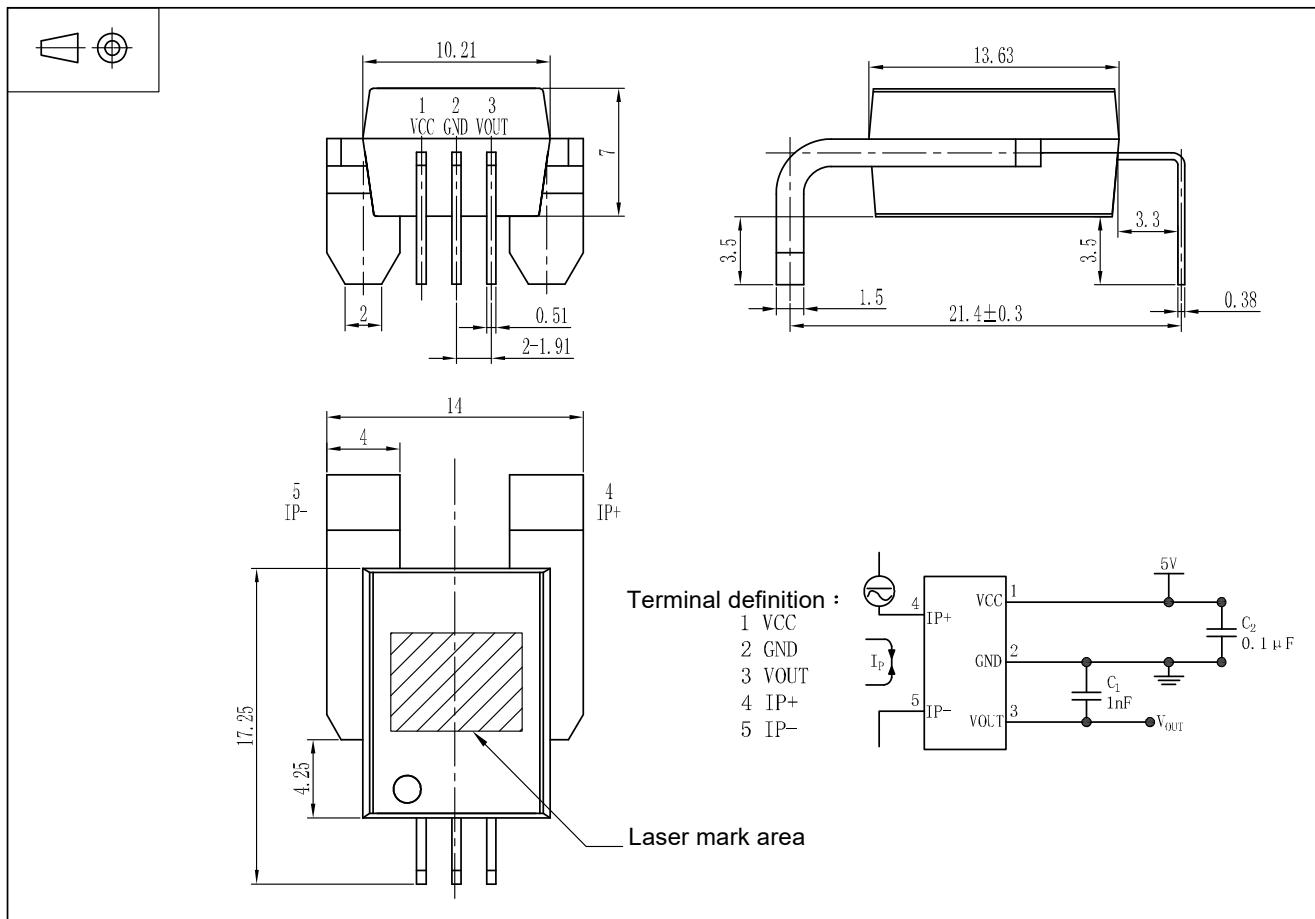
Mechanical characteristics

✧　General tolerance　　　　±0.3 mm
✧　Conductor and pin material　Red copper with tin plating

Remarks

✧　When I_P flows in the direction of pin4 to pin5，V_{out} increase.

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